

# Si3443DV

## P-Channel 2.5V Specified PowerTrench® MOSFET

### General Description

This P-Channel 2.5V specified MOSFET is produced using Fairchild's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

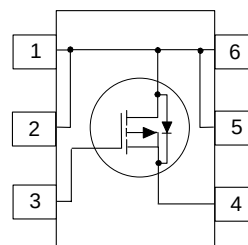
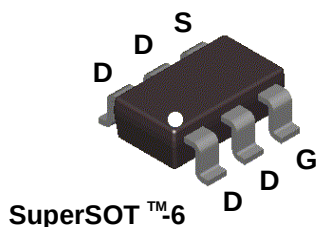
These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the larger packages are impractical.

### Applications

- Load switch
- Battery protection
- Power management

### Features

- -4 A, -20 V.  $R_{DS(ON)} = 0.065 \Omega @ V_{GS} = -4.5 \text{ V}$   
 $R_{DS(ON)} = 0.100 \Omega @ V_{GS} = -2.5 \text{ V}$
- Fast switching speed.
- Low gate charge (7.2nC typical).
- High performance trench technology for extremely low  $R_{DS(ON)}$ .
- SuperSOT™-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).



### Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter                                                     | Ratings     | Units            |
|----------------|---------------------------------------------------------------|-------------|------------------|
| $V_{DSS}$      | Drain-Source Voltage                                          | -20         | V                |
| $V_{GSS}$      | Gate-Source Voltage                                           | $\pm 8$     | V                |
| $I_D$          | Drain Current - Continuous (Note 1)                           | -4          | A                |
|                | Drain Current - Pulsed (Note 1a)                              | -20         |                  |
| $P_D$          | Power Dissipation for Single Operation (Note 1a)<br>(Note 1b) | 1.6         | W                |
|                |                                                               | 0.8         |                  |
| $T_J, T_{stg}$ | Operating and Storage Junction Temperature Range              | -55 to +150 | $^\circ\text{C}$ |

### Thermal Characteristics

|                 |                                                   |    |                    |
|-----------------|---------------------------------------------------|----|--------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1a) | 78 | $^\circ\text{C/W}$ |
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case (Note 1)     | 30 | $^\circ\text{C/W}$ |

### Package Outlines and Ordering Information

| Device Marking | Device   | Reel Size | Tape Width | Quantity   |
|----------------|----------|-----------|------------|------------|
| .443           | Si3443DV | 7"        | 8mm        | 3000 units |

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

**Off Characteristics**

|                                      |                                           |                                                                    |     |     |      |                      |
|--------------------------------------|-------------------------------------------|--------------------------------------------------------------------|-----|-----|------|----------------------|
| $BV_{DSS}$                           | Drain-Source Breakdown Voltage            | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$               | -20 |     |      | V                    |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = -250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$ |     | -16 |      | mV/ $^\circ\text{C}$ |
| $I_{DSS}$                            | Zero Gate Voltage Drain Current           | $V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$                       |     |     | -1   | $\mu\text{A}$        |
| $I_{GSSF}$                           | Gate-Body Leakage Current, Forward        | $V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$                         |     |     | 100  | nA                   |
| $I_{GSSR}$                           | Gate-Body Leakage Current, Reverse        | $V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$                        |     |     | -100 | nA                   |

**On Characteristics** (Note 2)

|                                        |                                                |                                                                                                                                                                      |      |                         |                         |                      |
|----------------------------------------|------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|-------------------------|-------------------------|----------------------|
| $V_{GS(th)}$                           | Gate Threshold Voltage                         | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$                                                                                                                     | -0.4 | -0.7                    | -1.5                    | V                    |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D = -250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$                                                                                                   |      | 2.5                     |                         | mV/ $^\circ\text{C}$ |
| $R_{DS(on)}$                           | Static Drain-Source On-Resistance              | $V_{GS} = -4.5\text{ V}, I_D = -4\text{ A}$<br>$V_{GS} = -4.5\text{ V}, I_D = -4\text{ A}, T_J = 125^\circ\text{C}$<br>$V_{GS} = -2.5\text{ V}, I_D = -3.2\text{ A}$ |      | 0.054<br>0.076<br>0.077 | 0.065<br>0.105<br>0.100 | $\Omega$             |
| $I_{D(on)}$                            | On-State Drain Current                         | $V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$                                                                                                                       | -10  |                         |                         | A                    |
| $g_{FS}$                               | Forward Transconductance                       | $V_{DS} = -5\text{ V}, I_D = -4\text{ A}$                                                                                                                            |      | 9                       |                         | S                    |

**Dynamic Characteristics**

|           |                              |                                                                      |  |     |  |    |
|-----------|------------------------------|----------------------------------------------------------------------|--|-----|--|----|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}$<br>$f = 1.0\text{ MHz}$ |  | 640 |  | pF |
| $C_{oss}$ | Output Capacitance           |                                                                      |  | 180 |  | pF |
| $C_{rss}$ | Reverse Transfer Capacitance |                                                                      |  | 90  |  | pF |

**Switching Characteristics** (Note 2)

|              |                     |                                                                                                   |  |     |    |    |
|--------------|---------------------|---------------------------------------------------------------------------------------------------|--|-----|----|----|
| $t_{d(on)}$  | Turn-On Delay Time  | $V_{DD} = -10\text{ V}, I_D = -1\text{ A}$<br>$V_{GS} = -4.5\text{ V}, R_{GEN} = 6\text{ }\Omega$ |  | 11  | 20 | ns |
| $t_r$        | Turn-On Rise Time   |                                                                                                   |  | 19  | 30 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time |                                                                                                   |  | 26  | 42 | ns |
| $t_f$        | Turn-Off Fall Time  |                                                                                                   |  | 35  | 55 | ns |
| $Q_g$        | Total Gate Charge   | $V_{DS} = -10\text{ V}, I_D = -4\text{ A}$<br>$V_{GS} = -4.5\text{ V}$                            |  | 7.2 | 10 | nC |
| $Q_{gs}$     | Gate-Source Charge  |                                                                                                   |  | 1.7 |    | nC |
| $Q_{gd}$     | Gate-Drain Charge   |                                                                                                   |  | 1.6 |    | nC |

**Drain-Source Diode Characteristics and Maximum Ratings**

|          |                                                       |                                                     |  |       |      |   |
|----------|-------------------------------------------------------|-----------------------------------------------------|--|-------|------|---|
| $I_S$    | Maximum Continuous Drain-Source Diode Forward Current |                                                     |  |       | -1.3 | A |
| $V_{SD}$ | Drain-Source Diode Forward Voltage                    | $V_{GS} = 0\text{ V}, I_S = -1.3\text{ A}$ (Note 2) |  | -0.75 | -1.2 | V |

**Notes:**

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

a)  $78^\circ\text{ C/W}$  when mounted on a  $1.0\text{ in}^2$  pad of 2 oz. copper.

b)  $156^\circ\text{ C/W}$  when mounted on a minimum pad of 2 oz. copper.

2. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

## Typical Characteristics

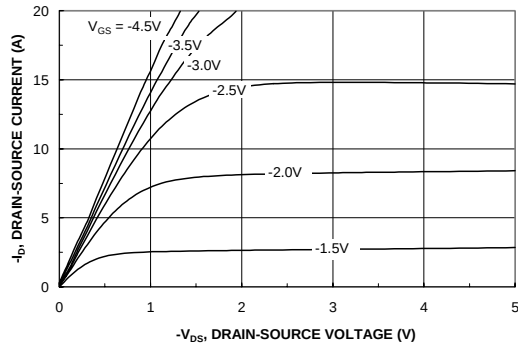


Figure 1. On-Region Characteristics.

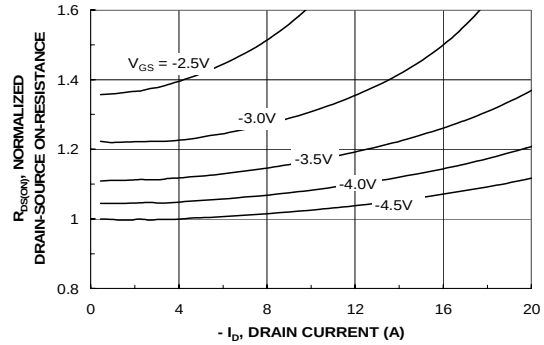


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

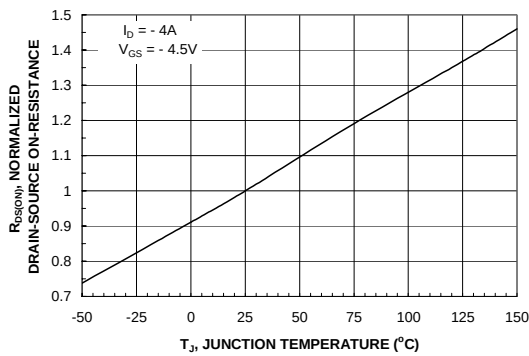


Figure 3. On-Resistance Variation with Temperature.

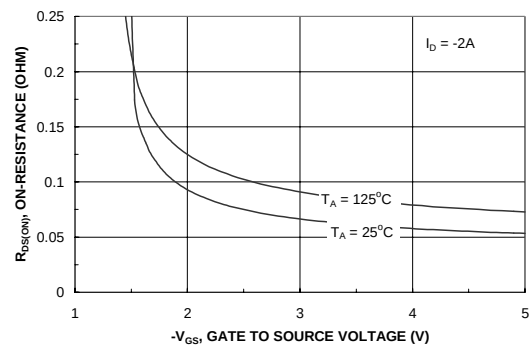


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

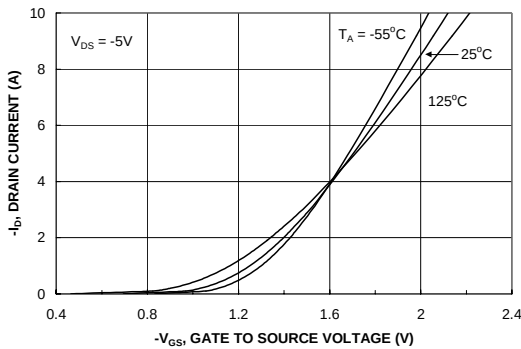


Figure 5. Transfer Characteristics.

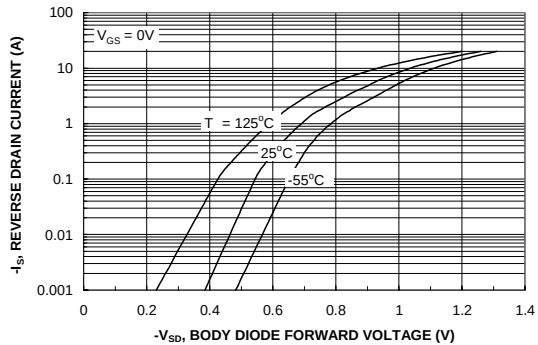


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics (continued)

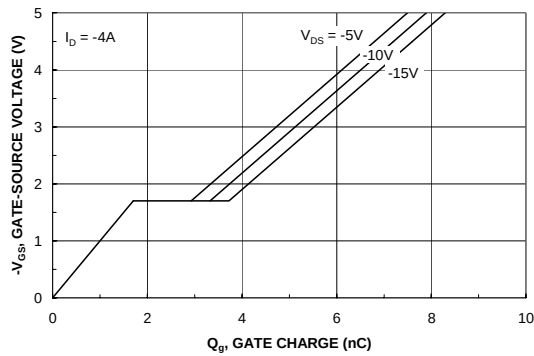


Figure 7. Gate-Charge Characteristics

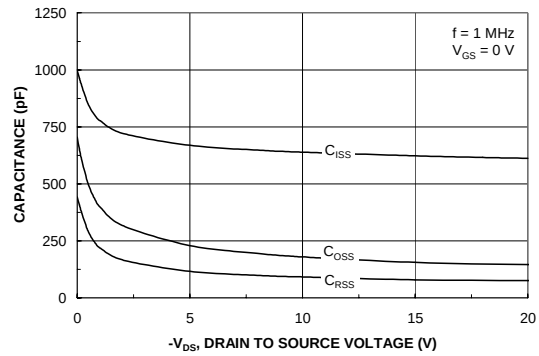


Figure 8. Capacitance Characteristics

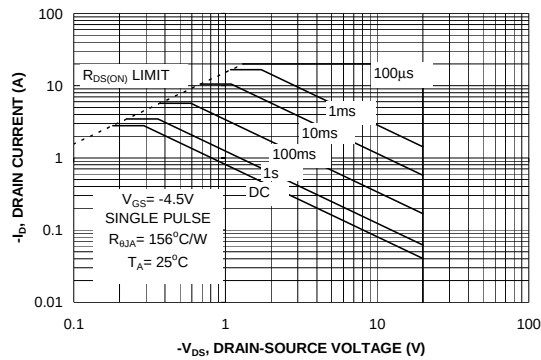


Figure 9. Maximum Safe Operating Area

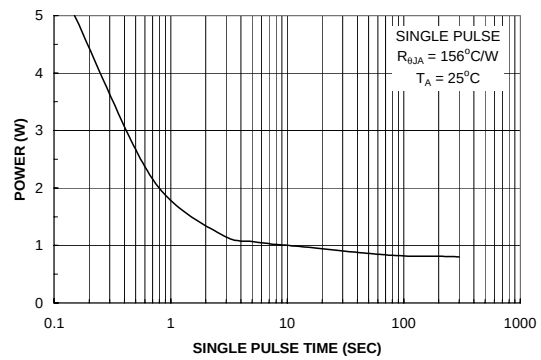


Figure 10. Single Pulse Maximum Power Dissipation

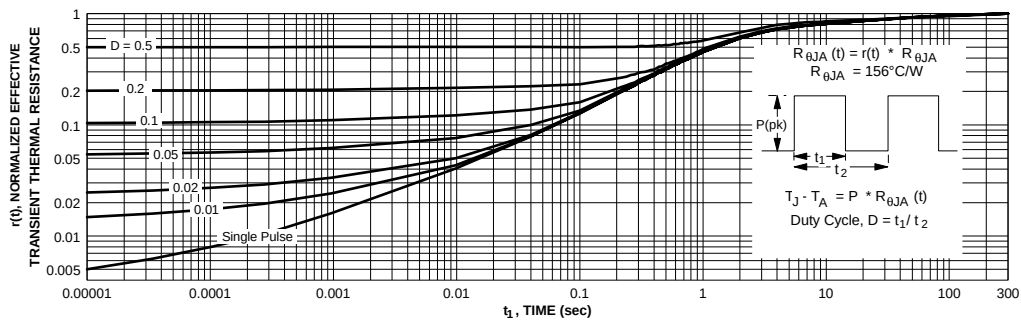


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.  
Transient thermal response will change depending on the circuit board design.

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